In the Specification:

Please replace the paragraph beginning at page 5, line 9, with the following amended paragraph:

Next, a well oxide layer (not shown) is formed on epitaxial layer 13. The well oxide layer preferably has a thickness on the order of about 100 to 500 Angstroms and may be thermally grown or deposited. An "active" nitride layer (not shown) is then deposited on the well oxide layer and preferably has a thickness on the order of about 1000 to 2000 Angstroms. Using standard photoresist techniques, portions of the well nitride layer are etched to expose portions of the well oxide layer surface. These exposed regions of the well oxide layer are then thermally oxidized to achieve a total oxide thickness on the order of about 3000 to 6000 Angstroms, forming field oxide regions 21A, 21B, and 21C, shown in FIG. 2. The remaining portions of the well nitride layer are removed using standard etching techniques or other methods known in the art, revealing well oxide layer 19 at active regions 22A and 22B. A technique that selectively removes the well nitride layer without significantly etching the well oxide layer disposed therebeneath is preferably employed. Although the number of field oxide regions and active regions may vary according to the desired semiconductor device structure, preferably at least one active region 22A is disposed over N+ buried layer 12.

Please replace the paragraph beginning at page 5, line 23, with the following amended paragraph:

Referring now to FIG. 3, using standard photoresist masking techniques, phosphorus or another suitable N-type dopant is selectively implanted into epitaxial layer 13 at active region 22B to form collector sinker 31. After implanting the N-type dopant, sinker 31 is annealed. Following the anneal of collector sinker 31, the well oxide layer 19 ~~(which now comprises active regions 22A and 22B)~~ is removed from the surface of epitaxial layer 13 in which the collector sinker has been formed.